

8 11. (Amended) The fabrication method of a semiconductor device according to claim 2, further comprising, after formation of said second insulation layer and before formation of said contact hole, the steps of:

forming a mask pattern on said second insulation layer,
etching said second insulation layer using said mask pattern to selectively reduce thickness of said second insulation layer, and
forming another mask pattern on said second insulation layer so as to expose a portion of the region reduced in thickness,
wherein said step of forming a contact hole includes the step of etching said second insulation layer using said another mask pattern, and
said step of forming a second conductive layer includes the step of forming a third conductive layer on said region reduced in thickness, electrically connected to said second conductive layer, in addition to formation of said second conductive layer.

Please add new claim 21 as follows.

21. (New) The fabrication method according to claim 1, wherein said first conductive layer is embedded only in said trench.